Philips Components

BUK455-400A
BUK455-400B

PowerMOS transistor

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a plastic envelope.
The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BUK455	-400A	-400B	
V_{DS}	Drain-source voltage	400	400	V
I_D	Drain current (DC)	7.3	6.5	A
P_{tot}	Total power dissipation	100	100	W
$R_{DS(ON)}$	Drain-source on-state resistance	0.8	1.0	Ω

MECHANICAL DATA

Dimensions in mm

Net Mass: 2g

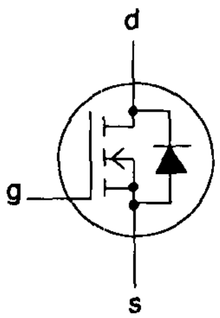
Pinning:

1 = Gate

2 = Drain

3 = Source

blue binder, tab 4



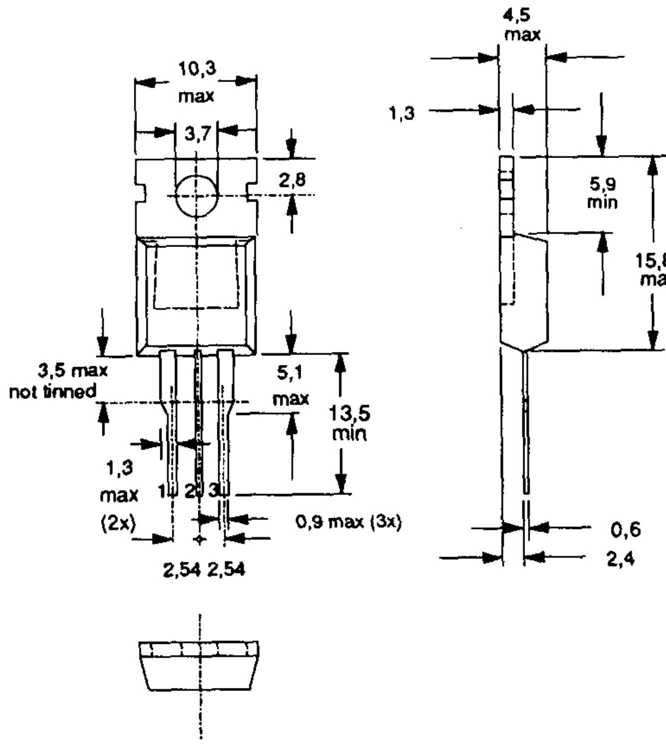


Fig.1 TO220AB; drain connected to mounting base.

Notes
1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Accessories supplied on request: refer to Mounting instructions for TO220 envelopes.

PHILIPS

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DS}	Drain-source voltage	-	-	400		V
V_{DGR}	Drain-gate voltage	R_{GS} = 20 kΩ	-	400		V
$\pm V_{GS}$	Gate-source voltage	-	-	30		V
				-400A	-400B	
I_D	Drain current (DC)	T_{mb} = 25 °C	-	7.3	6.5	A
I_D	Drain current (DC)	T_{mb} = 100 °C	-	4.6	4.1	A
I_{DM}	Drain current (pulse peak value)	T_{mb} = 25 °C	-	29	26	A
P_{tot}	Total power dissipation	T_{mb} = 25 °C	-	100		W
T_{stg}	Storage temperature	-	- 55	150		°C
T_j	Junction Temperature	-	-	150		°C

THERMAL RESISTANCES

From junction to mounting base	$R_{th\,j-mb}$ = 1.25 K/W
From junction to ambient	$R_{th\,j-a}$ = 60 K/W

STATIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA	400	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 400 V; V_{GS} = 0 V; T_j = 25 °C	-	2	20	µA
I_{DSS}	Zero gate voltage drain current	V_{DS} = 400 V; V_{GS} = 0 V; T_j =125 °C	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	V_{GS} = ±30 V; V_{DS} = 0 V	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; I_D = 2.5 A BUK455-400A	-	0.7	0.8	Ω
		BUK455-400B	-	0.9	1.0	Ω

DYNAMIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 25 V; I_D = 2.5 A	3.5	4.5	-	S
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	750	1000	pF
C_{oss}	Output capacitance		-	120	180	pF
C_{rss}	Feedback capacitance		-	50	70	pF
$t_{d\,on}$	Turn-on delay time	V_{DD} = 30 V; I_D = 2.7 A;	-	10	25	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_{GS} = 50 Ω;	-	25	40	ns
$t_{d\,off}$	Turn-off delay time	R_{gen} = 50 Ω	-	120	140	ns
t_f	Turn-off fall time		-	40	65	ns
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

REVERSE DIODE RATINGS AND CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	7.3	A
I_{DRM}	Pulsed reverse drain current	-	-	-	29	A
V_{SD}	Diode forward voltage	I_F = 7.3 A ; V_{GS} = 0 V	-	1.1	1.5	V
t_{rr}	Reverse recovery time	I_F = 7.3 A; $-dI_F/dt$ = 100 A/µs;	-	1200	-	ns
Q_{rr}	Reverse recovery charge	V_{GS} = 0 V; V_R = 100 V	-	6.0	-	µC

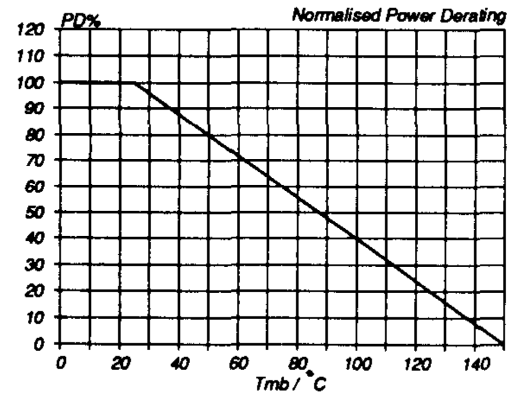


Fig.2. Normalised power dissipation.
$PD\% = 100 \cdot P_D/P_{D\,25\,°C} = f(T_{mb})$

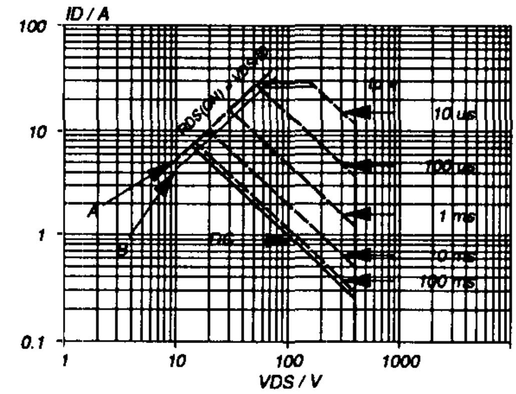


Fig.4. Safe operating area. T_{mb} = 25 °C
I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

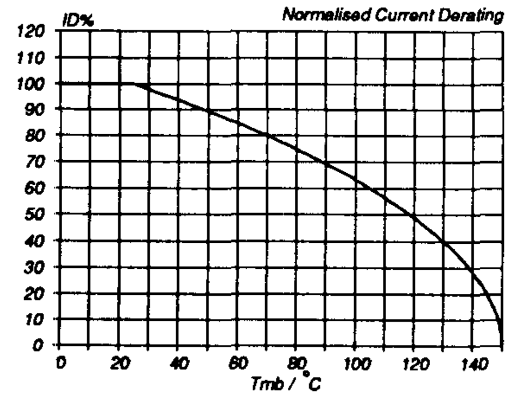


Fig.3. Normalised continuous drain current.
$ID\% = 100 \cdot I_D/I_{D\,25\,°C} = f(T_{mb})$; conditions: $V_{GS} \geq 10$ V

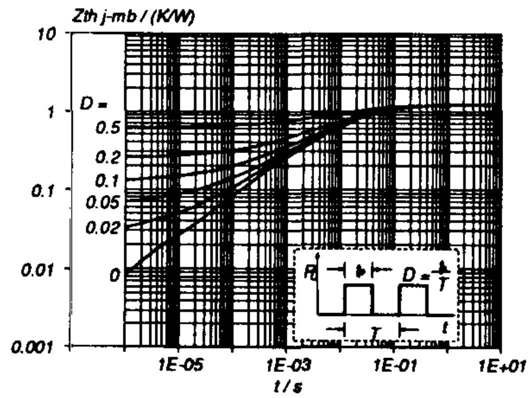


Fig.5. Transient thermal impedance.
$Z_{th\,j\text{-}mb} = f(t)$; parameter $D = t_p/T$

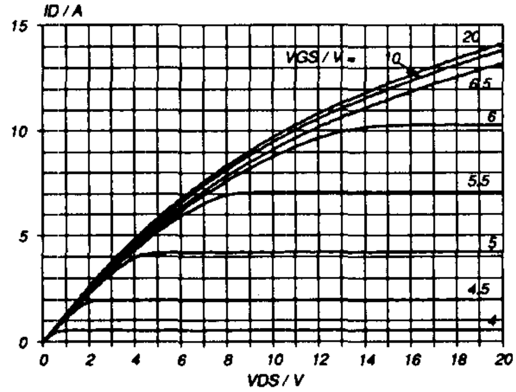


Fig.6.[1] Typical output characteristics, $T_j = 25$ °C.
$I_D = f(V_{DS})$; parameter V_{GS}

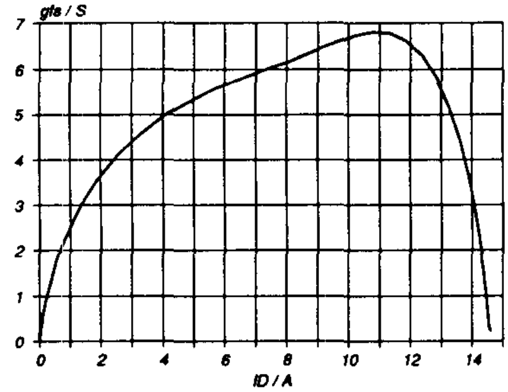


Fig.9. Typical transconductance, $T_j = 25$ °C.
$g_{fs} = f(I_D)$; conditions: $V_{DS} = 25$ V

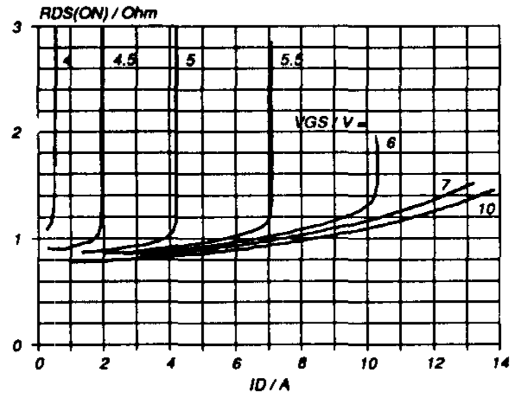


Fig.7. Typical on-state resistance, $T_j = 25$ °C.
$R_{DS(ON)} = f(I_D)$; parameter V_{GS}

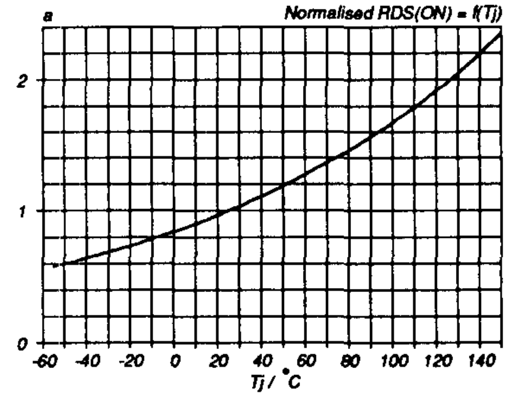


Fig.10. Normalised drain-source on-state resistance.
$a = R_{DS(ON)}/R_{DS(ON)25\,°C} = f(T_j)$; $I_D = 2.5$ A; $V_{GS} = 10$ V

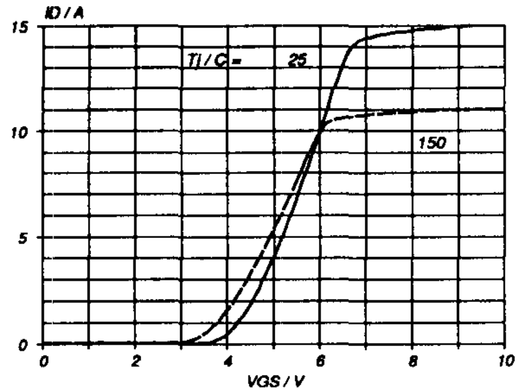


Fig.8. Typical transfer characteristics.
$I_D = f(V_{GS})$; conditions: $V_{DS} = 25$ V; parameter T_j

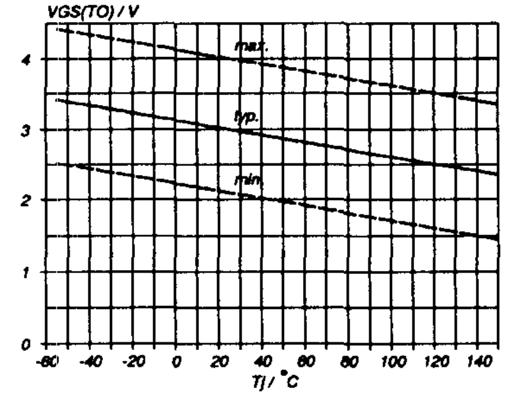


Fig.11. Gate threshold voltage.
$V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1$ mA; $V_{DS} = V_{GS}$

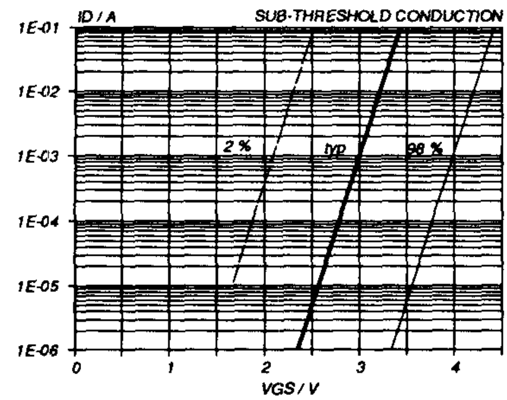


Fig.12. Sub-threshold drain current.
$I_D = f(V_{GS})$; conditions: $T_j = 25\ ^\circ C$; $V_{DS} = V_{GS}$

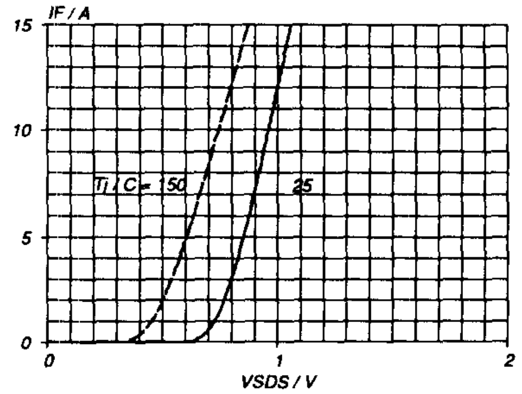


Fig.15. Typical reverse diode current.
$I_F = f(V_{SDS})$; conditions: $V_{GS} = 0$ V; parameter T_j

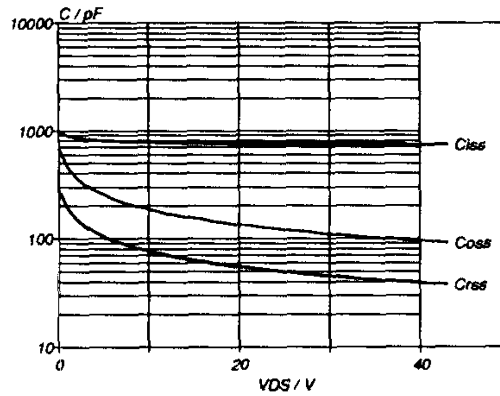


Fig.13. Typical capacitances, C_{iss}, C_{oss}, C_{rss}.
$C = f(V_{DS})$; conditions: $V_{GS} = 0$ V; f = 1 MHz

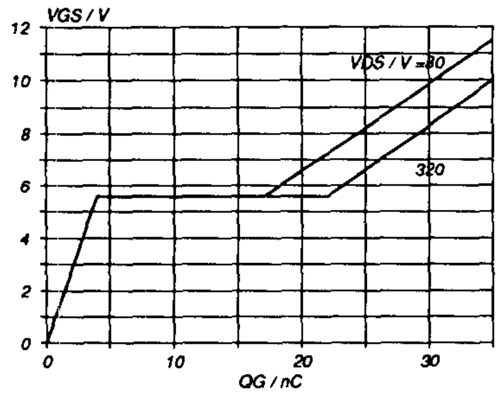


Fig.14. Typical turn-on gate-charge characteristics.
$V_{GS} = f(Q_G)$; conditions: $I_D = 6.5$ A; parameter V_{DS}